



ZXMN3A01F

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C		
30V	0.12Ω @ $V_{GS} = 10V$	2.0A		

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Motor Control

Features

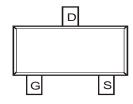
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

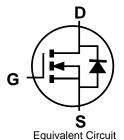
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 (3)
- Lead Free Plating (Matte Tin Finish Annealed over Alloy 42 Leadframe)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Top View



Top View Pin Configuration



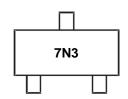
Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMN3A01FTA	SOT23	3,000/Tape & Reel
ZXMN3A01FTC	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7N3 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

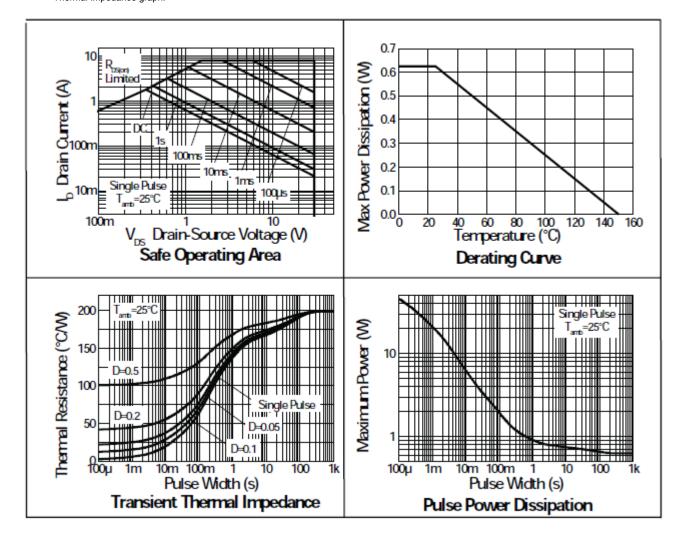
Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current, V _{GS} = 10V	I _D	2.0 1.6 1.8	А		
Pulsed Drain Current (Note 7)			I_{DM}	8	Α
Maximum Body Diode Continuous Current (Note 6)	I _S	1.3	Α		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	P _D	625	mW	
Linear Derating Factor	(Note 3)		5	mW/°C	
Total Power Dissipation (Note 6)			806	mW	
Linear Derating Factor	(Note 6)	P _D	6.4	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	7	200	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	155		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t≤5 secs.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

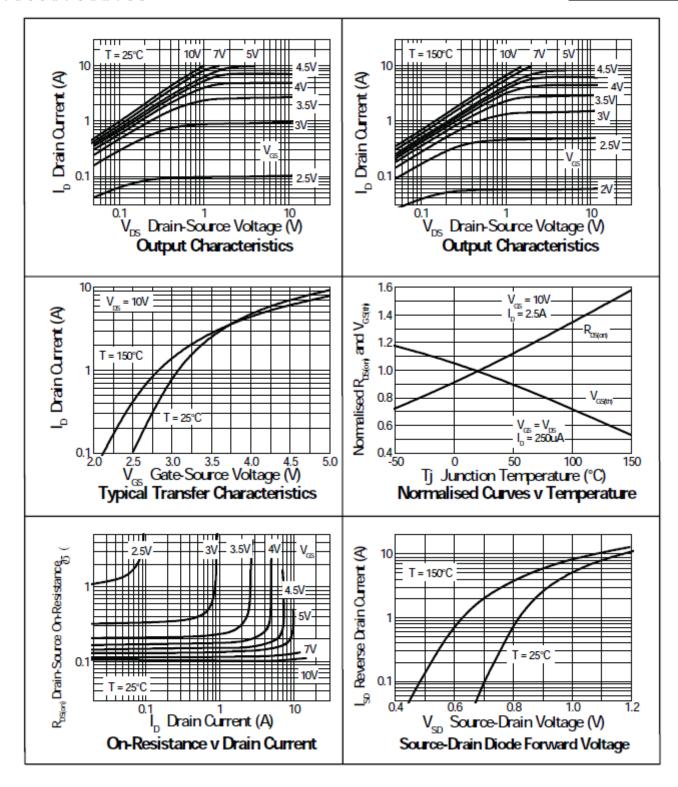
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	Dec. (a) ii		0.11	0.12	Ω	$V_{GS} = 10V, I_D = 2.5A$	
Static Drain-Source On-Nesistance (Note 6)	R _{DS(ON)}		_	0.18	Ω	$V_{GS} = 4.5V, I_D = 2A$	
Forward Transconductance	g FS		3.5	_	S	$V_{DS} = 4.5V, I_D = 2.5A$	
Diode Forward Voltage (Note 8 & 10)	V_{SD}	_	0.85	0.95	V	$V_{GS} = 0V$, $I_S = 1.7A$, $T_J = +25$ °C	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	190			V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	38		pF		
Reverse Transfer Capacitance	Crss	_	20			1 - 1101112	
Gate Charge (Note 9)	Q_g		2.3	_		$V_{DS} = 15V, V_{GS} = 5V, I_D = 2.5A$ $V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 2.5A$	
Total Gate Charge (Note 9)	Q_g	_	3.9	_	nC		
Gate-Source Charge (Note 9)	Q_{gs}		0.6	_	110		
Gate-Drain Charge (Note 9)	Q_{gd}	_	0.9	_			
Turn-On Delay Time (Note 9)	t _{D(on)}	_	1.7	_		$V_{DD} = 15V$, $I_{D} = 2.5A$, $R_{G} = 6\Omega$, $V_{GS} = 10V$	
Turn-On Rise Time (Note 9)	t _r	_	2.3	_			
Turn-Off Delay Time (Note 9)	t _{D(off)}	_	6.6	_	ns		
Turn-Off Fall Time (Note 9)	t _f	_	2.9	_			
Reverse Recovery Time	t _{rr}	_	17.7	_	ns	T 125°C 2.5\ di/dt 400\\/	
Reverse Recovery Charge	Qrr	_	13	_	nC	$T_J = +25$ °C, $I_F = 2.5$ A, $di/dt = 100$ A/ μ s	

Notes:

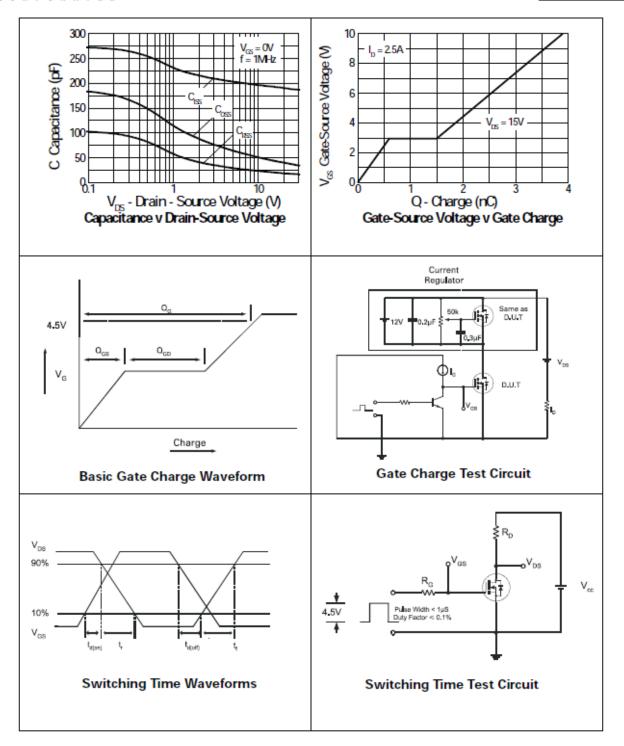
- 8. Measured under pulsed conditions. Width=300µs. Duty cycle \leq 2%.
- 9. Switching characteristics are independent of operating junction temperature.

 10. Guaranteed by design. Not subject to production testing.





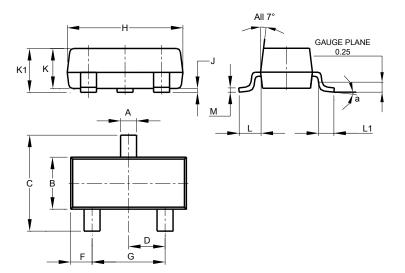






Package Outline Dimensions

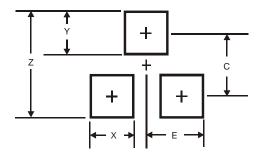
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	8°					
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35



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